

ABSTRACT OF THE DISCLOSURE

It is an object to provide a technique for removing a resist favorably without leaving residue in the case of using a nonaqueous resist stripper. According to the present invention, in order to achieve the object, when a resist pattern is removed by using the 5 nonaqueous resist stripper, it becomes easier to remove the resist pattern after dry etching or ion doping, by performing exposure treatment on the resist pattern. After a resist pattern is formed from a DNQ-novolac resin type of positive resist composition, the resist pattern is irradiated with light within the range of photosensitive wavelength of the DNQ photosensitizer, thereby removing the resist pattern with the nonaqueous resist stripper.

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